

# R6076ENZ1

## Nch 600V 76A Power MOSFET

$V_{\mathrm{DSS}}$	600V
R <sub>DS(on)</sub> (Max.)	$0.042\Omega$
I <sub>D</sub>	76A
$P_D$	120W

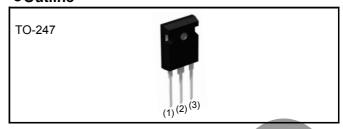
#### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage ( $V_{GSS}$ ) guaranteed to be  $\pm 20V$ .
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

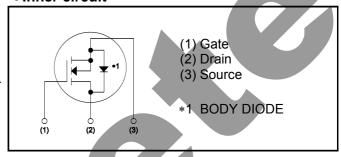
# Application

**Switching Power Supply** 

#### Outline



### ●Inner circuit



T dona	or ackaging specifications					
	Packaging	Tube				
	Reel size (mm)	-				
Typo	Tape width (mm)	-				
Type	Basic ordering unit (pcs)	450				
	Taping code	C9				
	Marking	R6076ENZ1				

# ●Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{ m DSS}$	600	V
Continuous drain current T <sub>c</sub> = 25°C	I <sub>D</sub> <sup>*1</sup>	±76	А
$T_c = 100^{\circ}C$	I <sub>D</sub> <sup>*1</sup>	±41.3	А
Pulsed drain current	I <sub>D,pulse</sub> *2	±228	А
Gate - Source voltage	$V_{GSS}$	±20	V
Avalanche energy, single pulse	E <sub>AS</sub> *3	1954	mJ
Avalanche energy, repetitive	E <sub>AR</sub> *3	2.96	mJ
Avalanche current, repetitive	I <sub>AR</sub>	13.4	Α
Power dissipation (T <sub>c</sub> = 25°C)	$P_{D}$	120	W
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	−55 to +150	°C
Reverse diode dv/dt	dv/dt *4	15	V/ns

## Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V$ $T_{j} = 125^{\circ}C$	50	V/ns

## ●Thermal resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Offit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.04	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	30	°C/W
Soldering temperature, wavesoldering for 10s	T <sub>sold</sub>		-	265	°C

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	OTIIL
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0V$ , $I_D = 1mA$	600	1	-	V
		$V_{DS} = 600V, V_{GS} = 0V$				
Zero gate voltage drain current	I <sub>DSS</sub>	T <sub>j</sub> = 25°C	-	0.1	100	μΑ
		T <sub>j</sub> = 125°C	-	-	1000	
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	1	ı	±100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS}$ = 10V, $I_D$ = 1mA	2	ı	4	V
		$V_{GS} = 10V, I_D = 44.4A$				
Static drain - source on - state resistance	$R_{DS(on)}^{}^{\star_5}}$	T <sub>j</sub> = 25°C	-	0.038	0.042	Ω
		T <sub>j</sub> = 125°C		0.085		
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	0.7	-	Ω

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i lettei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g <sub>fs</sub> *5	$V_{DS} = 10V, I_{D} = 38A$	22.5	45.0	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	6500	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 25V	-	4700	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	520	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V	-	235		
Effective output capacitance, time related	C <sub>o(tr)</sub>	V <sub>DS</sub> = 0V to 480V		1210		pF
Turn - on delay time	t <sub>d(on)</sub> *5	$V_{DD} \simeq 300V$ , $V_{GS} = 10V$		65	-	
Rise time	t <sub>r</sub> *5	I <sub>D</sub> = 38A	<b>-</b>	170	-	no
Turn - off delay time	t <sub>d(off)</sub> *5	$R_L = 7.87\Omega$	-	450	-	ns
Fall time	t <sub>f</sub> *5	$R_G = 10\Omega$	-	170	-	

# •Gate Charge characteristics $(T_a = 25^{\circ}C)$

Parameter	Symbol Conditions		Values			Unit
r ai ai nietei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Qg *5	V <sub>DD</sub> ≈ 300V	-	260	1	
Gate - Source charge	Q <sub>gs</sub> *5	I <sub>D</sub> = 50A	-	40	-	nC
Gate - Drain charge	Q <sub>gd</sub> *5	V <sub>GS</sub> = 10V	-	135	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq 300V$ , $I_D = 50A$	-	6.0	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup>  $P_W \leq 10 \mu s,$  Duty cycle  $\leq 1\%$ 

<sup>\*3</sup>  $I_D$  = 13.4A,  $V_{DD}$  = 50V

<sup>\*4</sup> Reference measurement circuits Fig.5-1.

<sup>\*5</sup> Pulsed

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	T <sub>c</sub> = 25°C	-	ı	76	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2	1 c = 20 G	-	-	228	A
Forward voltage	V <sub>SD</sub> *5	V <sub>GS</sub> = 0V, I <sub>S</sub> = 76A	-	-	1.5	V
Reverse recovery time	t <sub>rr</sub> *5		-	990	-	ns
Reverse recovery charge	Q <sub>rr</sub> *5	I <sub>S</sub> = 76A di/dt = 100A/μs	-	32	1	μС
Peak reverse recovery current	I <sub>rrm</sub> *5			65	-	Α

# ●Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R <sub>th1</sub>	0.0691		C <sub>th1</sub>	0.0406	
R <sub>th2</sub>	0.427	K/W	C <sub>th2</sub>	0.873	Ws/K
R <sub>th3</sub>	0.250		C <sub>th3</sub>	19.9	

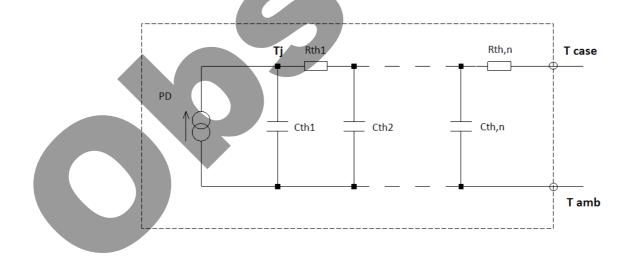
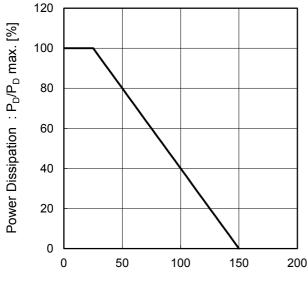
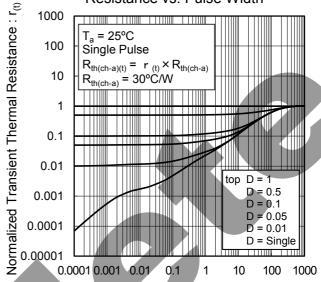


Fig.1 Power Dissipation Derating Curve



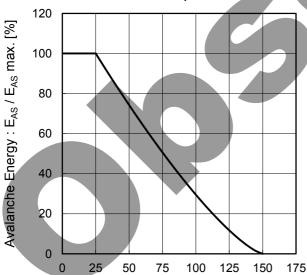
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Normalized Transient Thermal Resistance vs. Pulse Width



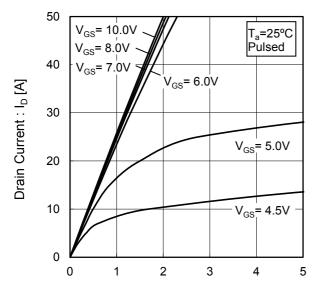
Pulse Width: P<sub>W</sub> [s]

Fig.3 Avalanche Energy Derating Curve vs Junction Temperature



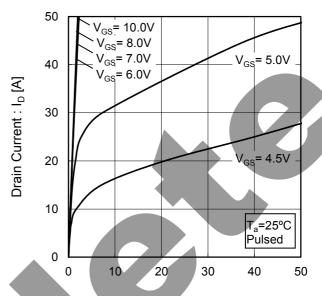
Junction Temperature : T<sub>i</sub> [°C]

Fig.4 Typical Output Characteristics(I)



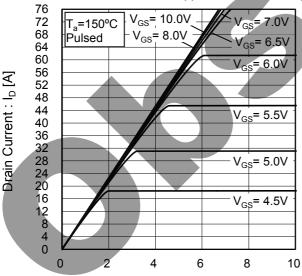
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.5 Typical Output Characteristics(II)



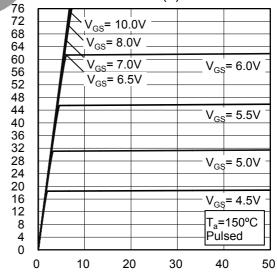
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.6 T<sub>j</sub> = 150°C Typical Output Characteristics(I)



Drain - Source Voltage :  $V_{DS}$  [V]

Fig.7  $T_j$  = 150°C Typical Output Characteristics(II)



Drain - Source Voltage : V<sub>DS</sub> [V]

Drain Current: I<sub>D</sub> [A]

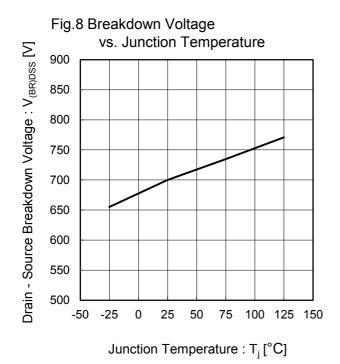


Fig.9 Typical Transfer Characteristics

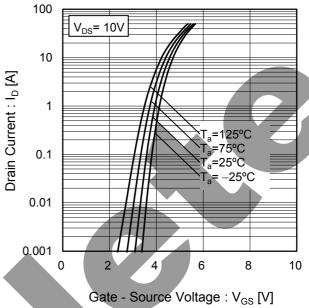


Fig.10 Gate Threshold Voltage vs. Junction Temperature

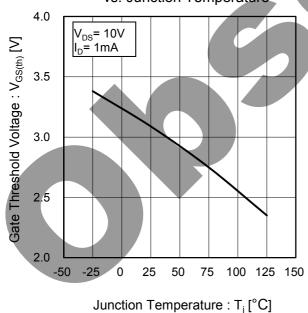


Fig.11 Transconductance vs. Drain Current

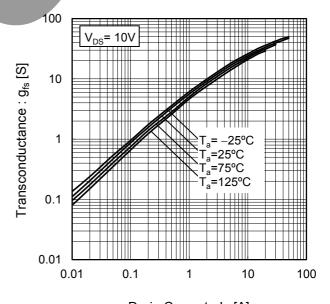
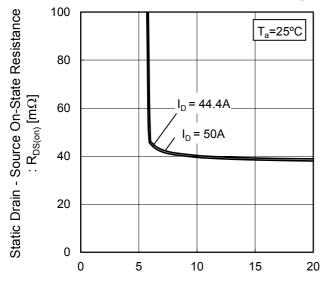
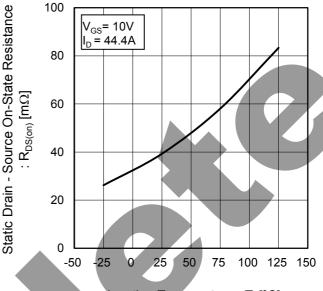


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



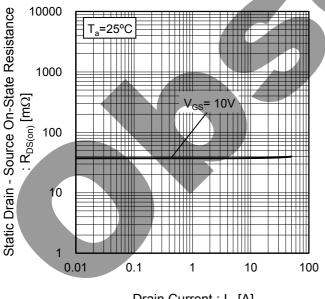
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature



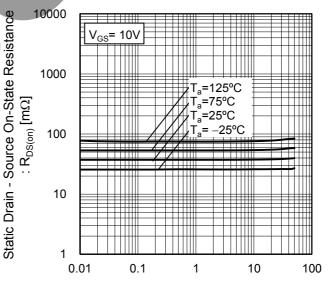
Junction Temperature : T<sub>i</sub> [°C]

Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



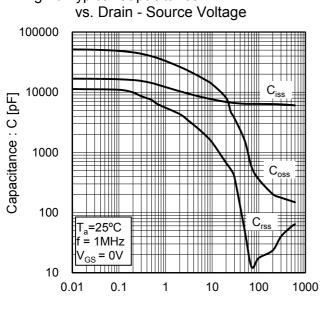
Drain Current :  $I_D$  [A]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current



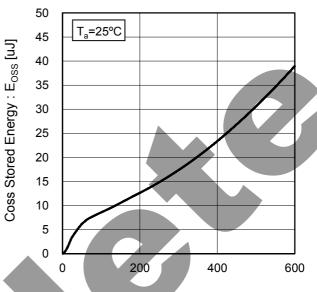
Drain Current : I<sub>D</sub> [A]

Fig.16 Typical Capacitance



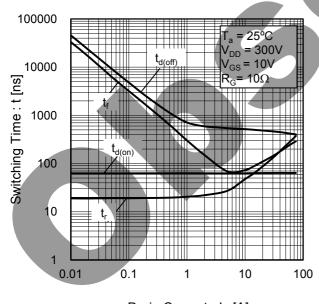
Drain - Source Voltage :  $V_{DS}$  [V]

Fig.17 Coss Stored Energy



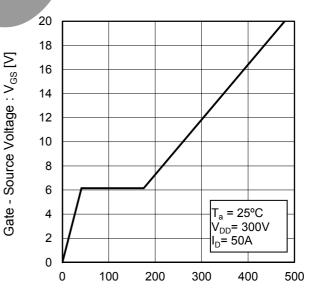
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.18 Switching Characteristics

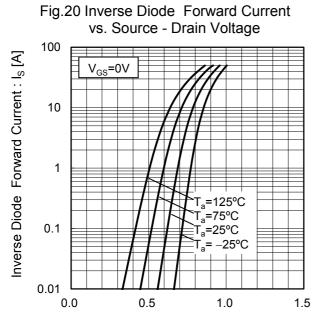


Drain Current : I<sub>D</sub> [A]

Fig.19 Dynamic Input Characteristics

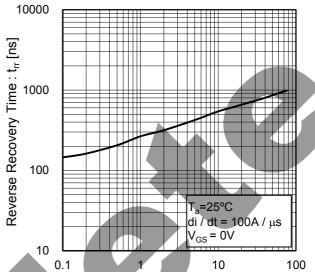


Total Gate Charge : Q<sub>g</sub> [nC]



Source - Drain Voltage :  $V_{SD}$  [V]

Fig.21 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]



### ●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

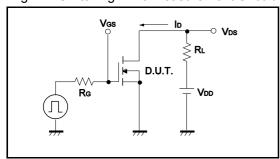


Fig.2-1 Gate Charge Measurement Circuit

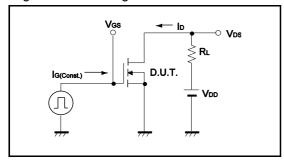


Fig.3-1 Avalanche Measurement Circuit

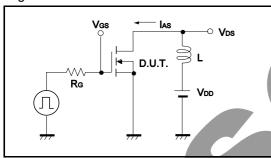


Fig.4-1 dv/dt Measurement Circuit

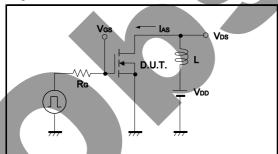


Fig.5-1 di/dt Measurement Circuit

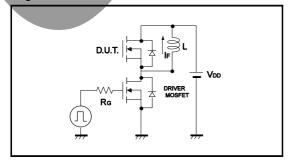


Fig.1-2 Switching Waveforms

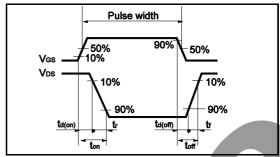


Fig.2-2 Gate Charge Waveform

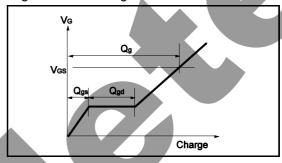


Fig.3-2 Avalanche Waveform

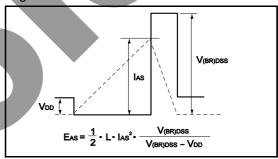


Fig.4-2 dv/dt Waveform

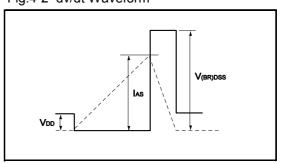
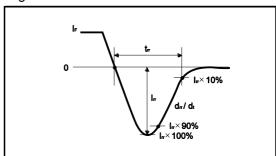
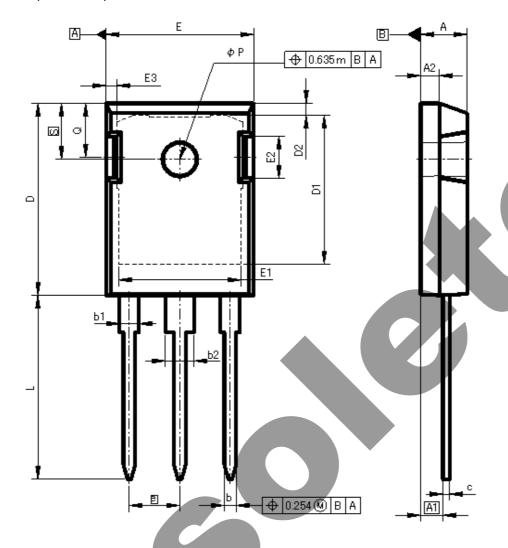


Fig.5-2 di/dt Waveform



# ●Dimensions (Unit : mm)

TO-247



DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.91	2.16	0.075	0.085
b	1.14	1.40	0.045	0.055
b1	1.91	2.20	0.075	0.087
b2	2.92	3.20	0.115	0.126
С	0.61	0.80	0.024	0.031
D	20.80	21.34	0.819	0.840
D1	17.43	17.83	0.686	0.702
E	15.75	16.13	0.620	0.635
е	5.4	45	0.215	
N	3.0	00	3.0	000
L	19.81	20.57	0.780	0.810
L1	3.81	4.32	0.150	0.170
ФР	3.55	3.65	0.140	0.144
Q	5.59	6.20	0.220	0.244
S	6.	15	0.2	40

Dimension in mm / inches

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JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSⅢ	CLASS II b	CLASSII
CLASSIV	CLASSIII	CLASSⅢ	CLASSIII

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  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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For details, please refer to ROHM Mounting specification

#### **Precautions Regarding Application Examples and External Circuits**

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
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  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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